TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS III)

TPC6103

Notebook PC Applications Portable Equipment Applications

• Low drain-source ON resistance: RDS (ON) = 29 m Ω (typ.)

• High forward transfer admittance: $|Y_{fs}| = 13 \text{ S (typ.)}$

• Low leakage current: $IDSS = -10 \mu A (max) (VDS = -12 V)$

• Enhancement mode: $V_{th} = -0.5 \text{ to } -1.2 \text{ V}$

 $(V_{\rm DS} = -10 \ \rm V, I_{\rm D} = -200 \ \mu A)$

Maximum Ratings (Ta = 25°C)

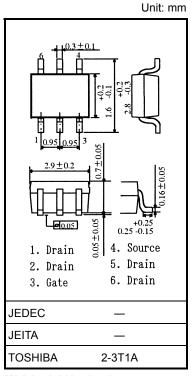
Characteris	itics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-12	V	
Drain-gate voltage (R _G	$S = 20 \text{ k}\Omega$)	V_{DGR}	-12	V	
Gate-source voltage		V _{GSS}	±8	V	
Drain current	DC (Note 1)	I _D	-5.5	Α	
Diam current	Pulse (Note 1)	I _{DP}	-22		
Drain power dissipation (t = 5 s) (Note 2a)		P_{D}	2.2	W	
Drain power dissipation (t = 5 s) (Note 2b)		P _D	0.7	W	
Single pulse avalanche	energy (Note 3)	E _{AS}	5.3	mJ	
Avalanche current		I _{AR}	-2.75	Α	
Repetitive avalanche e	nergy (Note 4)	E _{AR}	0.22	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature ra	inge	T _{stg}	-55~150	°C	

Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to ambient $(t = 5 s)$ (Note 2a)	R _{th (ch-a)}	56.8	°C/W	
Thermal resistance, channel to ambient $(t = 5 s)$ (Note 2b)	R _{th (ch-a)}	178.5	°C/W	

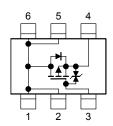
Note 1, (ote 2, Note 3, Note 4 and Note 5: See the next page.

This transistor is an electrostatic-sensitive device. Please handle with caution.



Weight: 0.011 g (typ.)

Circuit Configuration



Electrical Characteristics (Ta = 25°C)

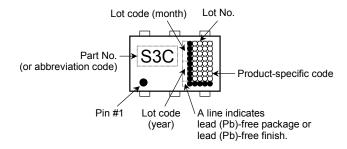
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА	
Drain cut-off curr	Drain cut-off current		$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μΑ	
Drain-source breakdown voltage		V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-12	_	_	V	
		V _{(BR)DSX}	$I_D = -10 \text{ mA}, V_{GS} = 8 \text{ V}$	-4			V	
Gate threshold ve	oltage	V _{th}	$V_{DS} = -10 \ V, \ I_D = -200 \ \mu A$	-0.5		-1.2	>	
			$V_{GS} = -1.8 \text{ V}, I_D = -1.4 \text{ A}$	_	65	90		
Drain-source ON resistance		R _{DS (ON)}	$V_{GS} = -2.5 \text{ V}, I_D = -2.8 \text{ A}$	_	42	55	mΩ	
		R _{DS (ON)}	$V_{GS} = -4.5 \text{ V}, I_D = -2.8 \text{ A}$	_	29	35		
Forward transfer	admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, I_D = -2.8 \text{ A}$	6.5	13		S	
Input capacitance		C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	1520		pF	
Reverse transfer capacitance		C _{rss}		_	330	_		
Output capacitance		Coss		_	380	_		
Switching time	Rise time	t _r	V _{GS} -5 V I _D = -2.8 A	_	9.5			
	Turn-on time	t _{on}		_	16		ns	
	Fall time	t _f		_	28		115	
	Turn-off time	t _{off}	$V_{DD} \simeq -6 \text{ V}$ Duty \leq 1%, $t_W =$ 10 μs	_	74			
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \simeq -10 \text{ V}, V_{GS} = -5 \text{ V},$	_	20			
Gate-source charge		Q _{gs}	$I_D = -5.5 \text{ A}$		15	_	nC	
Gate-drain ("miller") charge		Q _{gd}		_	5	_		

Source-Drain Ratings and Characteristics (Ta = 25°C)

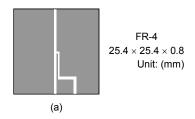
Characteristics Symbol		Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	I _{DRP}	_	_	_	-22	Α
Forward voltage (diode) V _{DSF}		V _{DSF}	$I_{DR} = -5.5 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V

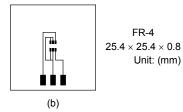
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Marking (Note 5)



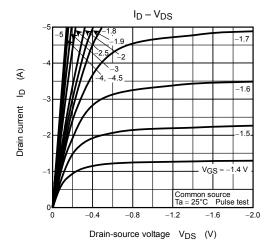
- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s) (b) Device mounted on a glass-epoxy board (b) (t = 5 s)

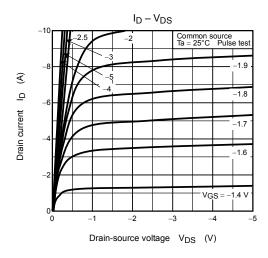


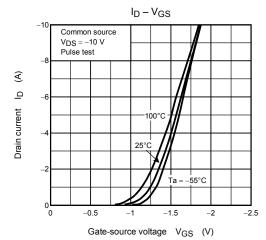


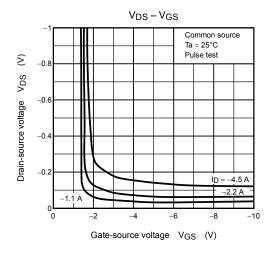
- Note 3: $V_{DD} = -10 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 0.5 mH, $R_G = 25 \Omega$, $I_{AR} = -2.75 \text{ A}$
- Note 4: Repetitive rating: pulse width limited by maximum channel temperature
- Note 5: on lower left of the marking indicates Pin 1.

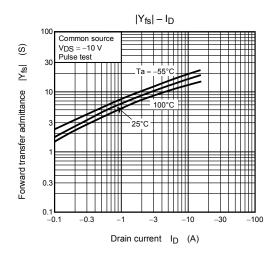
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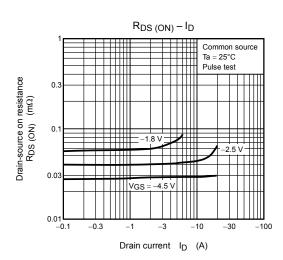


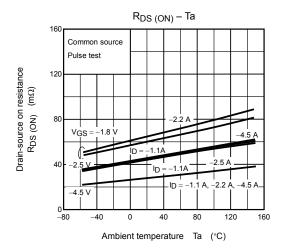


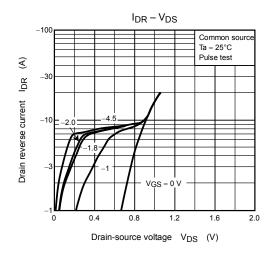


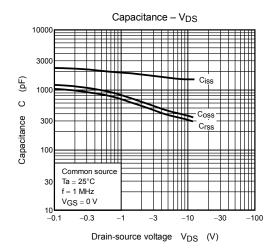


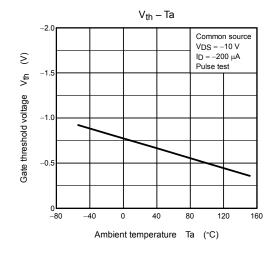


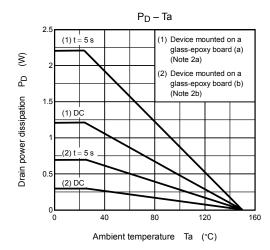


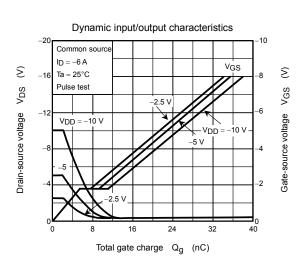




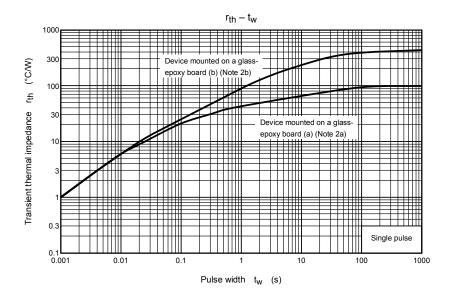


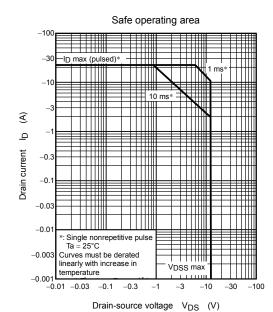






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Handbook" etc..

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